

anisotropic etching, and the rf bias voltage to which a peak to peak voltage V_{pp} value larger than a V_{pp} value of a continuous rf bias voltage at which the same etch rate can be obtained is given, so as to have the high ion energy which is larger than a high ion energy of the continuous rf bias voltage, is applied to a stage on which a sample is placed independently of the generation of the plasma; and

on-off modulating the rf bias voltage at a region in which anisotropy is high before a region in which selectivity is high.

Please cancel claims 2 and 5-7 without prejudice or disclaimer of the subject matter thereof.

Please amend claim 29 as follows:

29. (amended) A method according to claim 1, wherein a saddle-shaped ion energy distribution is provided having the at least one peak point of the region of the low ion energy and the at least one peak point of the region of the high ion energy separated by a region of the intermediate ion energy.

Please add the following new claim:

30. A method according to claim 1, wherein the at least one peak point of the region of the high ion energy and the at least one peak point of the region of the low ion energy has a number of ions which is at least twice a number of ions in a region of the intermediate ion energy.--

REMARKS

By the above amendment, claim 1 has been amended to clarify features of the present invention and to overcome the rejection under 35 U.S.C. §112, claims 2 and 5-7 have been canceled without prejudice or disclaimer of the subject matter